



2SA1478/2SC3788

High-Definition CRT Display Video Output Applications

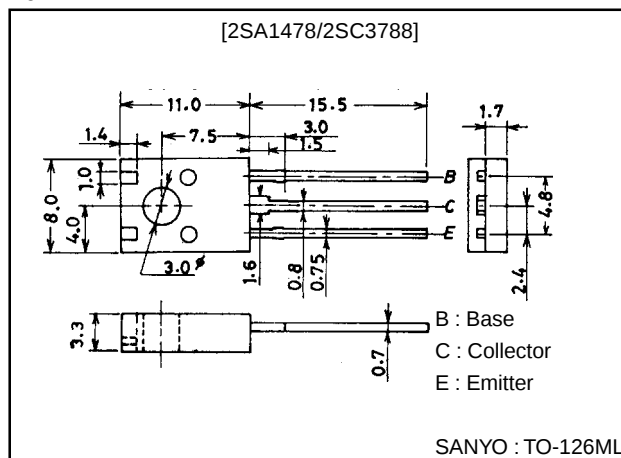
Features

- High breakdown voltage : $V_{CEO} \geq 200V$.
- Small reverse transfer capacitance and excellent high frequency characteristic
: $C_{re} = 1.2pF$ (NPN), $1.7pF$ (PNP).
- Adoption of FBET process.

Package Dimensions

unit:mm

2042A



() : 2SA1478

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)200	V
Collector-to-Emitter Voltage	V_{CEO}		(-)200	V
Emitter-to-Base Voltage	V_{EBO}		(-)5	V
Collector Current	I_C		(-)100	mA
Peak Collector Current	I_{CP}		(-)200	mA
Collector Dissipation	P_C	$T_c = 25^\circ C$	1.3	W
			5	W
Junction Temperature	T_j		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)150V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)10V, I_C = (-)10mA$	40*		320*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)30V, I_C = (-)10mA$		150		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)30V, f = 1MHz$		1.7		pF
				(2.6)		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = (-)30V, f = 1MHz$		1.2		pF
				(1.7)		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)0.6	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)20mA, I_B = (-)2mA$			(-)1.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)200			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)200			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V

* : The 2SA1478/2SC3788 are classified by 10mA h_{FE} as follows:

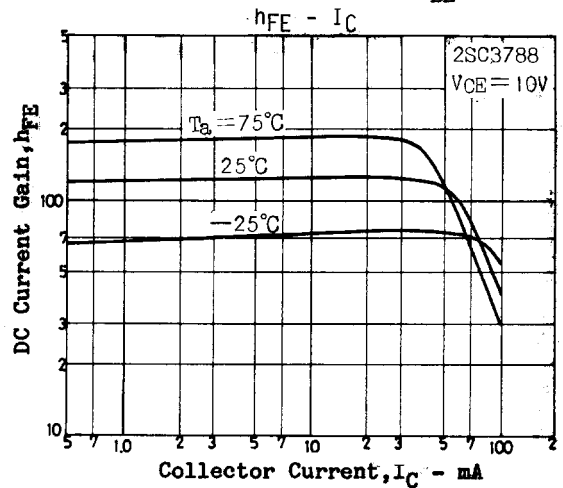
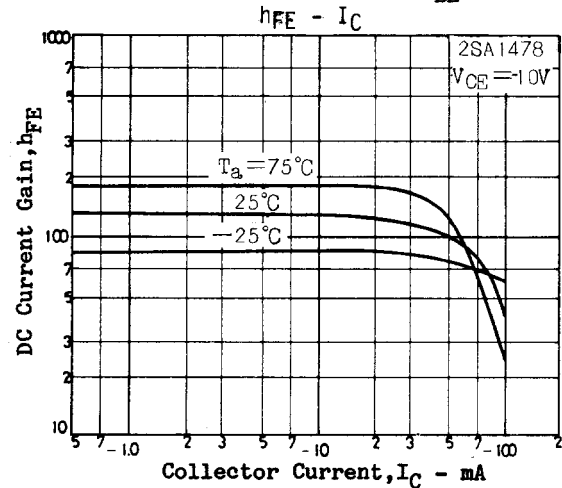
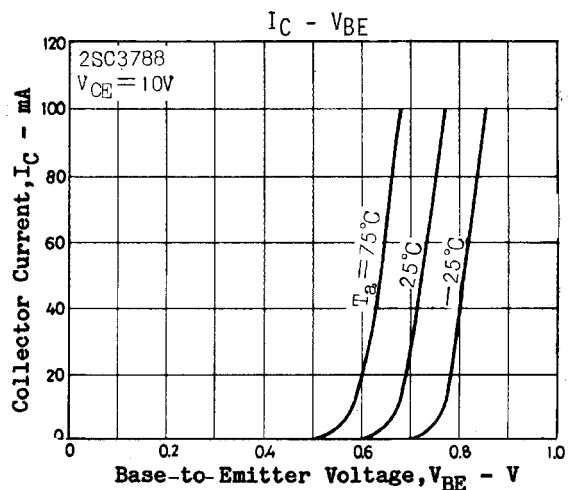
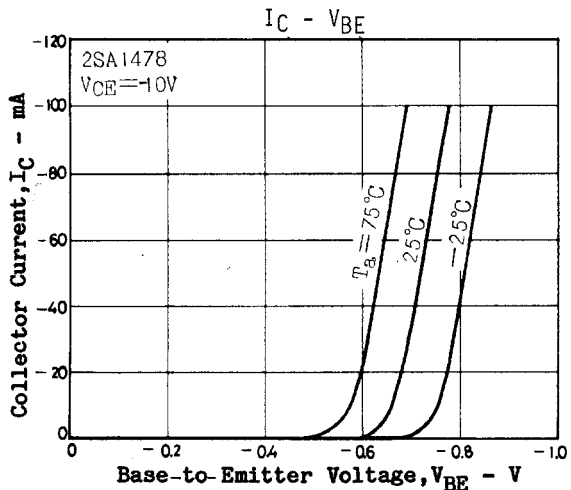
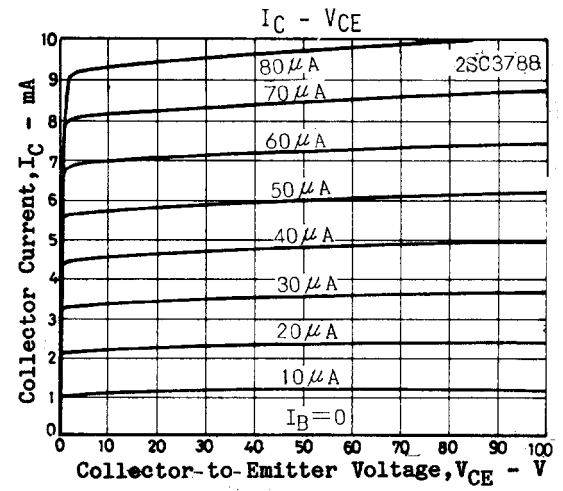
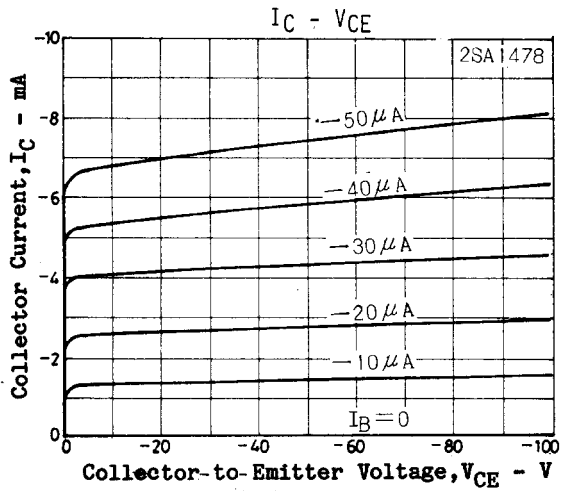
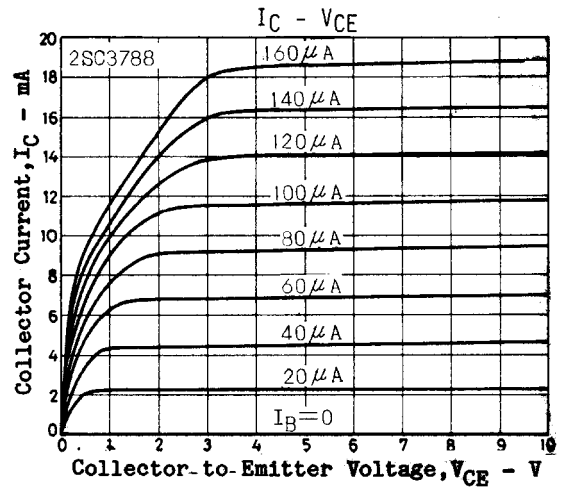
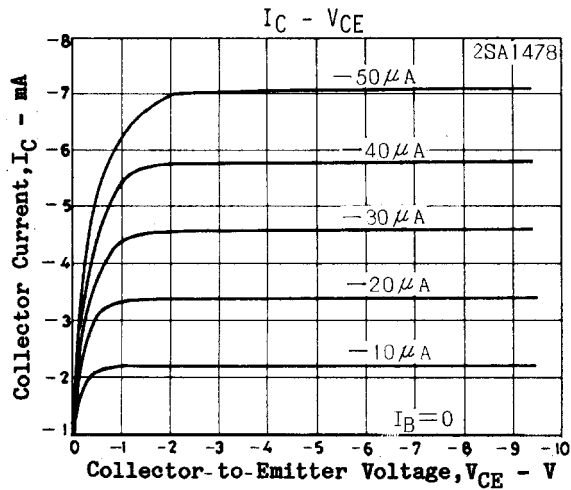
40	C	80	60	D	120	100	E	200	160	F	320
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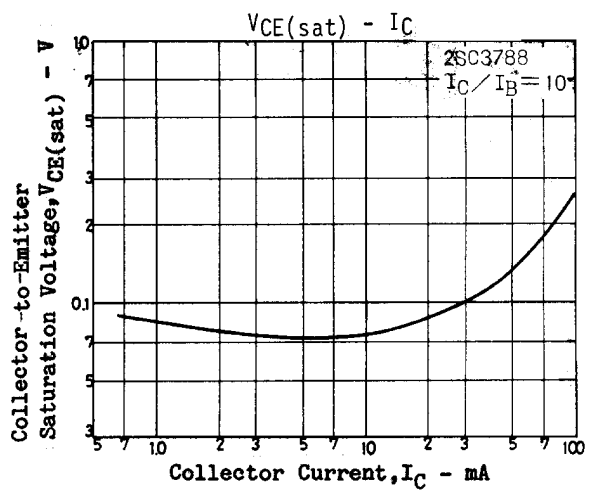
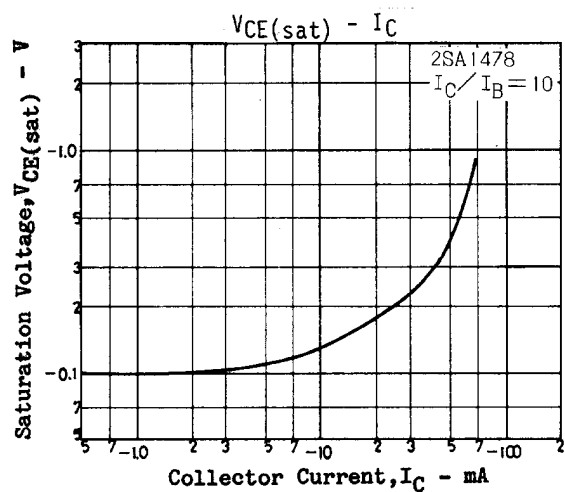
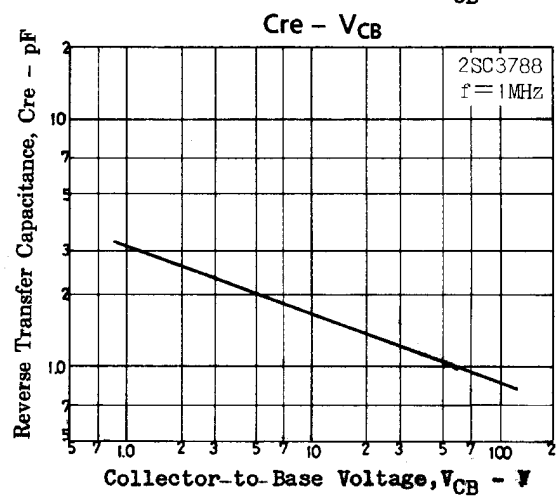
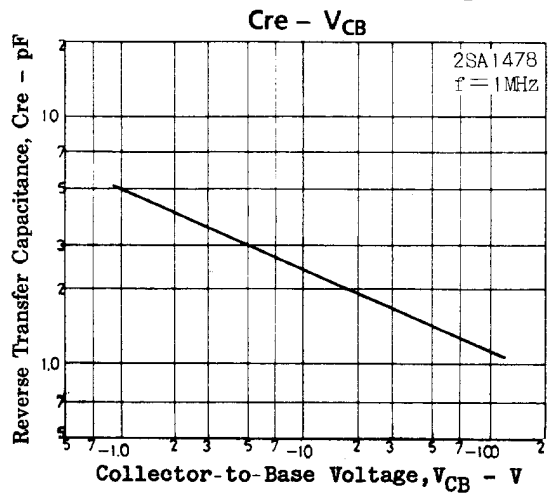
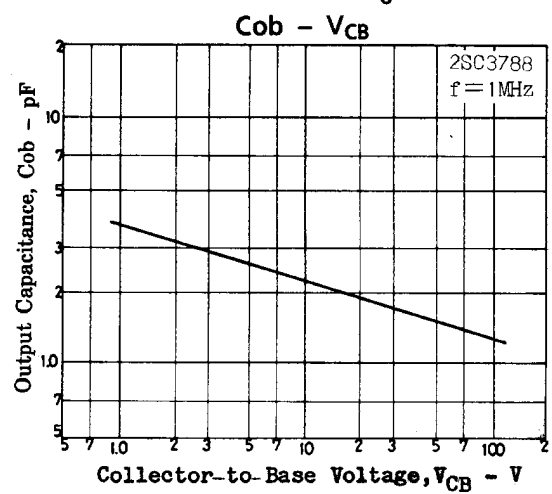
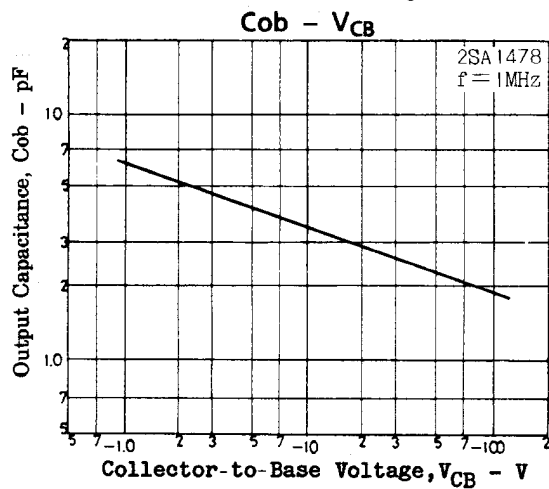
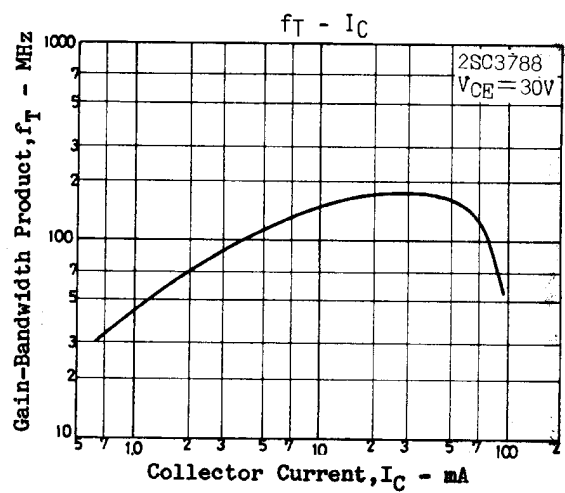
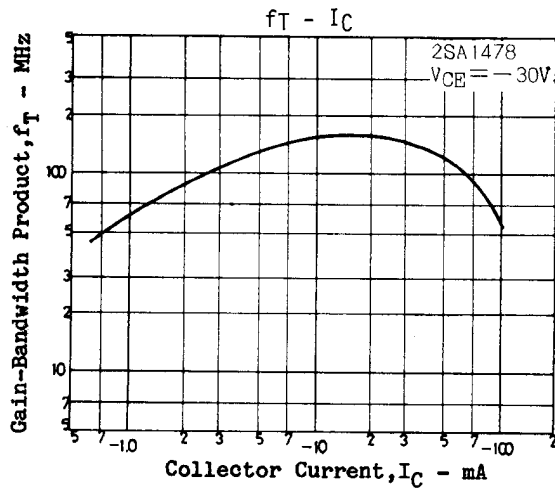
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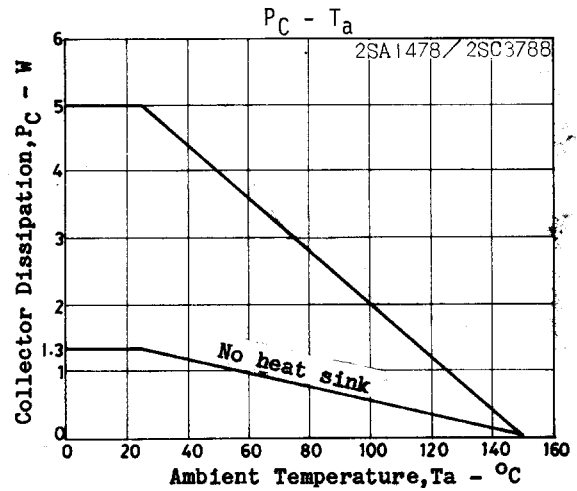
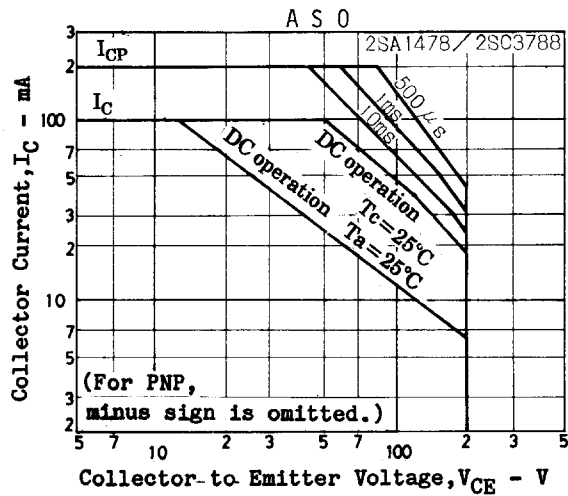
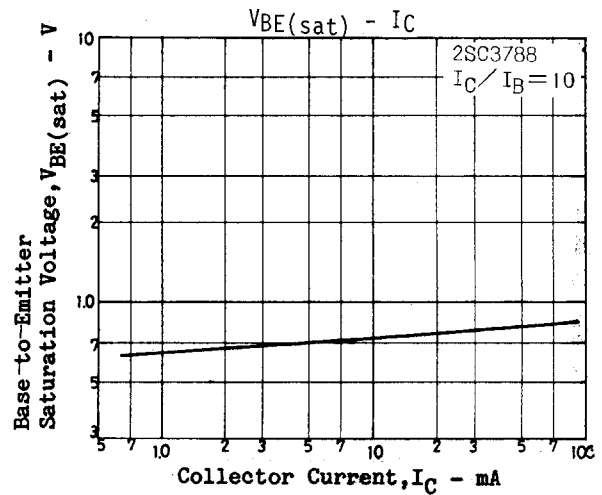
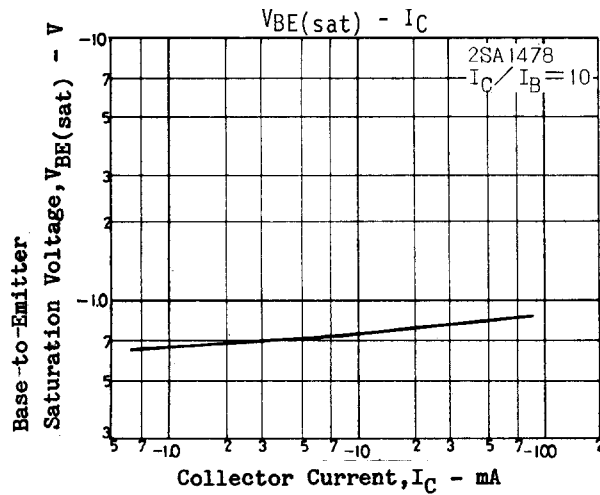
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